

PNP Silicon Epitaxial Planar Transistor

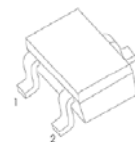
Features:

- A collector current is large.
 - Collector saturation voltage is low.
- $-V_{CE(sat)}$: 250mV(Max.) at $-I_C=200mA$ / $-I_B=10mA$

MARKING: BW

SOT-523

1. BASE
2. EMITTER
3. COLLECTOR



MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector- Base Voltage	-15	V
V_{CEO}	Collector-Emitter Voltage	-12	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-0.5	A
P_C	Collector Power Dissipation	0.15	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55-150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-15			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-12			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-15V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-2V, I_C=-10mA$	270		680	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-200mA, I_B=-10mA$			-0.25	V
Transition frequency	f_T	$V_{CE}=-2V, I_C=-10mA, f=100MHz$		260		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		6.5		pF

Typical Characteristics

